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# 2SC4367

Silicon NPN Epitaxial

# HITACHI

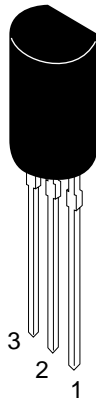
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## Application

High Frequency amplifier

## Outline

TO-92MOD



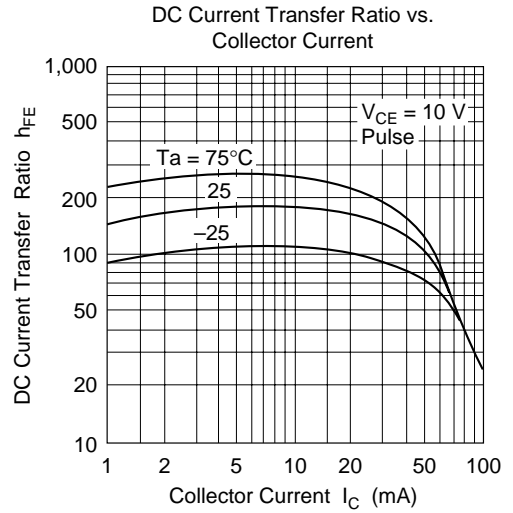
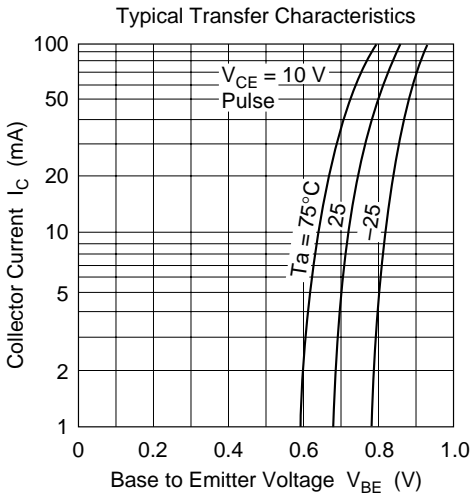
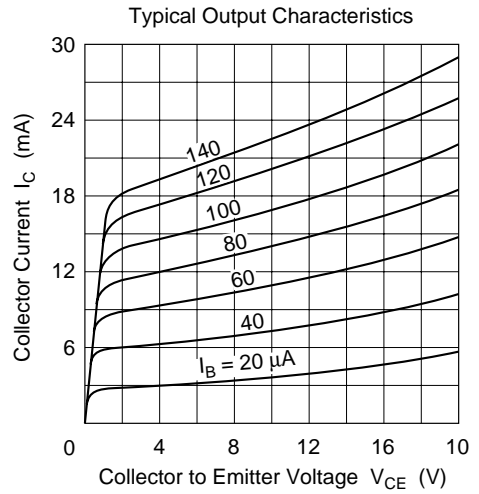
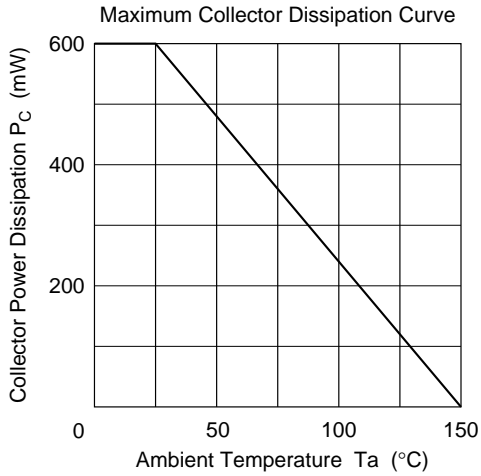
- 1. Emitter
- 2. Collector
- 3. Base

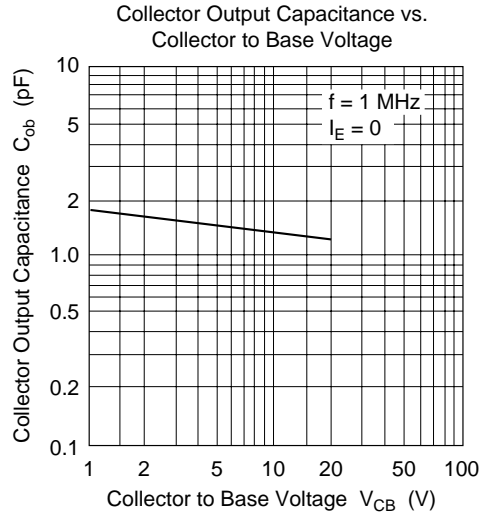
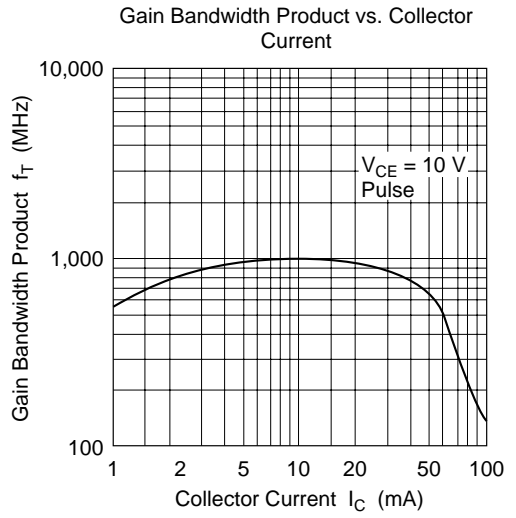
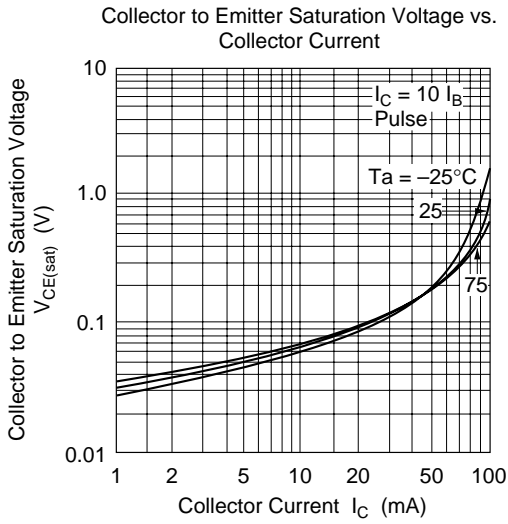
**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	30	V
Collector to emitter voltage	$V_{\text{CEO}}$	20	V
Emitter to base voltage	$V_{\text{EBO}}$	3	V
Collector current	$I_{\text{C}}$	100	mA
Collector peak current	$i_{\text{C (peak)}}$	200	mA
Collector power dissipation	$P_{\text{C}}$	600	mW
Junction temperature	$T_{\text{j}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	30	—	—	V	$I_{\text{C}} = 10 \mu\text{A}$ , $I_{\text{E}} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	20	—	—	V	$I_{\text{C}} = 3 \text{ mA}$ , $R_{\text{BE}} = \infty$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	3	—	—	V	$I_{\text{E}} = 10 \mu\text{A}$ , $I_{\text{C}} = 0$
Collector cutoff current	$I_{\text{CBO}}$	—	—	1.0	$\mu\text{A}$	$V_{\text{CB}} = 10 \text{ V}$ , $I_{\text{E}} = 0$
DC current transfer ratio	$h_{\text{FE}}$	40	—	—		$V_{\text{CE}} = 10 \text{ V}$ , $I_{\text{C}} = 10 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	—	1.0	V	$I_{\text{C}} = 20 \text{ mA}$ , $I_{\text{B}} = 4 \text{ mA}$
Gain bandwidth product	$f_{\text{T}}$	600	1000	—	MHz	$V_{\text{CE}} = 10 \text{ V}$ , $I_{\text{C}} = 10 \text{ mA}$
Collector output capacitance	$C_{\text{ob}}$	—	1.3	—	pF	$V_{\text{CB}} = 10 \text{ V}$ , $I_{\text{E}} = 0$ , $f = 1 \text{ MHz}$







Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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